

Attorney Docket # 10961260-3

a [single] shallow region which extends to the surface of the substrate, the shallow region comprising:

a protective outer wall adjacent to the substrate;

an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall; and

the shallow region having a shallow region cross-sectional area; wherein the deep region cross-sectional area is greater than the shallow region cross-sectional area, the deep region abutting only a single shallow region.

5. (Amended) A semiconductor isolation structure comprising:

a substrate, the substrate comprising a surface;

a first device and a second device formed within the substrate;

an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:

a deep region which extends into the substrate, the deep region comprising an oxide;

a [single] shallow region which extends to the surface of the substrate, the shallow region comprising:

a protective outer wall adjacent to the substrate,

an inner sealing wall located exclusively within the shallow region

and adjacent to the protective outer wall;

wherein the deep region abuts only a single shallow region, *and does not abut additional deep regions*

A replacement copy of the claims is included following the Applicants' response.